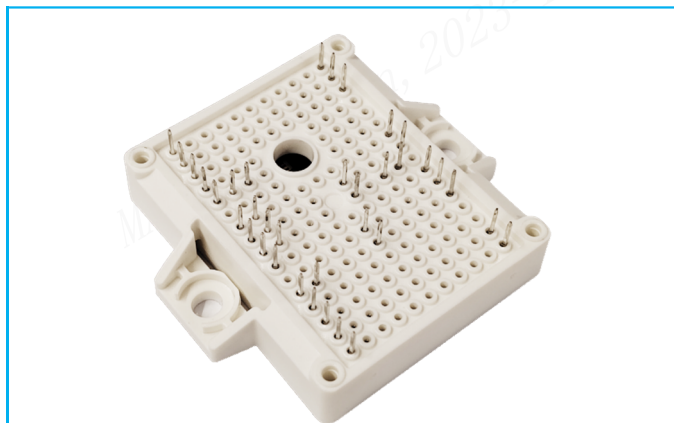


PRODUCT FEATURES

- ☐ 650V IGBT CHIP(Trench+Field Stop technology)
- ☐ Low saturation voltage and positive temperature coefficient
- ☐ Low switching losses and short tail current
- ☐ Free wheeling diodes with fast and soft reverse recovery
- ☐ Temperature sense included

APPLICATIONS

- ☐ 3-Level-Applications
- ☐ Solar Applications
- ☐ UPS Systems



IGBT(T1、 T2、 T3、 T4)

ABSOLUTE MAXIMUM RATINGS($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J=25^{\circ}\text{C}$	650	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C=25^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	200	A
I_{CM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	400	
P_{tot}	Power Dissipation Per IGBT	$T_C=25^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	588	W

Diode(D2、 D3、 D5、 D6)

ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^{\circ}\text{C}$	650	V
$I_{F(AV)}$	Average Forward Current		150	A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ms}$	300	
I_{FSM}		$T_J=125^{\circ}\text{C}, t=10\text{ms}, 50\text{Hz}$	633	A
I^2t			2000	A^2s

Diode(D1、 D4)

ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^{\circ}\text{C}$	650	V
$I_{F(AV)}$	Average Forward Current		120	A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ms}$	450	
I_{FSM}		$T_J=125^{\circ}\text{C}, t=10\text{ms}, 50\text{Hz}$	480	A
I^2t			1152	A^2s

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IGBT(T1、T4)

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Emitter Threshold Voltage	V _{CE} =V _{GE} , I _C =2.4mA	3.25	4.00	4.75	V
V _{CE(sat)}	Collector Emitter Saturation Voltage	I _C =100A, V _{GE} =15V, T _J =25℃		1.2	1.41	
		I _C =100A, V _{GE} =15V, T _J =125℃		1.25		
		I _C =100A, V _{GE} =15V, T _J =150℃		1.28		
I _{CES}	Collector Leakage Current	V _{CE} =650V, V _{GE} =0V, T _J =25℃			1	mA
I _{GES}	Gate Leakage Current	V _{CE} =0V,V _{GE} =±20V, T _J =25℃	-400		400	nA
R _{Gint}	Integrated Gate Resistor			0		Ω
Q _G	Gate Charge	V _{CE} =400V, I _C =100A , V _{GE} =15V		0.45		μC
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f =100kHz		14		nF
C _{res}	Reverse Transfer Capacitance			90		pF
t _{d(on)}	Turn on Delay Time	V _{CC} =300V,I _C =100A R _{Gon} =5.1Ω, V _{GE} =±15V, Inductive Load	T _J =25℃		20	ns
			T _J =125℃		22	ns
			T _J =150℃		22	ns
t _r	Rise Time		T _J =25℃		15	ns
			T _J =125℃		20	ns
			T _J =150℃		20	ns
t _{d(off)}	Turn off Delay Time		T _J =25℃		500	ns
			T _J =125℃		570	ns
			T _J =150℃		600	ns
t _f	Fall Time		T _J =25℃		40	ns
			T _J =125℃		50	ns
			T _J =150℃		55	ns
E _{on}	Turn on Energy	T _J =25℃		1.4	mJ	
		T _J =125℃		2.3	mJ	
		T _J =150℃		2.4	mJ	
E _{off}	Turn off Energy	T _J =25℃		1.45	mJ	
		T _J =125℃		1.55	mJ	
		T _J =150℃		1.6	mJ	
I _{SC}	Short Circuit Current	tpsc≤0μs , V _{GE} =15V T _J =150℃,V _{CC} =360V		1600		A
R _{thJC}	Junction to Case Thermal Resistance （ Per IGBT ）				0.255	K /W
R _{thJH}	Junction to heatsink with SE8117 （ Per IGBT ）			0.497		K /W

IGBT(T2、T3)

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Emitter Threshold Voltage	V _{CE} =V _{GE} , I _C =2.4mA	3.25	4.00	4.75	V
V _{CE(sat)}	Collector Emitter Saturation Voltage	I _C =100A, V _{GE} =15V, T _J =25℃		1.2	1.41	
		I _C =100A, V _{GE} =15V, T _J =125℃		1.25		
		I _C =100A, V _{GE} =15V, T _J =150℃		1.28		
I _{CES}	Collector Leakage Current	V _{CE} =650V, V _{GE} =0V, T _J =25℃			1	mA
I _{GES}	Gate Leakage Current	V _{CE} =0V,V _{GE} =±20V, T _J =25℃	-400		400	nA
R _{Gint}	Integrated Gate Resistor			0		Ω
Q _G	Gate Charge	V _{CE} =400V, I _C =100A , V _{GE} =15V		0.45		μC
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f =100kHz		14		nF
C _{res}	Reverse Transfer Capacitance			90		pF
t _{d(on)}	Turn on Delay Time	V _{CC} =300V,I _C =100A R _{Gon} =5.1Ω, V _{GE} =±15V, Inductive Load	T _J =25℃		20	ns
			T _J =125℃		22	ns
			T _J =150℃		22	ns
t _r	Rise Time		T _J =25℃		15	ns
			T _J =125℃		20	ns
			T _J =150℃		20	ns
t _{d(off)}	Turn off Delay Time		T _J =25℃		500	ns
			T _J =125℃		570	ns
			T _J =150℃		600	ns
t _f	Fall Time		T _J =25℃		50	ns
			T _J =125℃		55	ns
			T _J =150℃		58	ns
E _{on}	Turn on Energy	T _J =25℃		0.75	mJ	
		T _J =125℃		0.79	mJ	
		T _J =150℃		0.81	mJ	
E _{off}	Turn off Energy	T _J =25℃		1.2	mJ	
		T _J =125℃		1.7	mJ	
		T _J =150℃		2	mJ	
I _{SC}	Short Circuit Current	tpsc≤0μs , V _{GE} =15V T _J =150℃,V _{CC} =360V		1600		A
R _{thJC}	Junction to Case Thermal Resistance （ Per IGBT ）				0.255	K /W
R _{thJH}	Junction to heatsink with SE8117 （ Per IGBT ）			0.497		K /W

Diode(D2、D3、D5、D6)

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V _F	Forward Voltage	I _F =100A , V _{GE} =0V, T _J =25℃		1.1	1.65	V
		I _F =100A , V _{GE} =0V, T _J =125℃		1		
		I _F =100A , V _{GE} =0V, T _J =150℃		0.95		
t _{rr}	Reverse Recovery Time	I _F =100A , V _R =300V dI _F /dt=-4500A/μs T _J =150℃		200		ns
I _{RRM}	Max. Reverse Recovery Current			270		A
Q _{RR}	Reverse Recovery Charge			28		μC
E _{rec}	Reverse Recovery Energy			9.2		mJ
R _{thJC}	Junction to Case Thermal Resistance （Per Diode）				0.426	K /W
R _{thJH}	Junction to heatsink with SE8117 （Per IGBT）			0.677		K /W

Diode(D1、D4)

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V _F	Forward Voltage	I _F =100A , V _{GE} =0V, T _J =25℃		1.35	2.2	V
		I _F =100A , V _{GE} =0V, T _J =125℃		1.5		
		I _F =100A , V _{GE} =0V, T _J =150℃		1.55		
t _{rr}	Reverse Recovery Time	I _F =100A , V _R =300V dI _F /dt=-3500A/μs T _J =150℃		25		ns
I _{RRM}	Max. Reverse Recovery Current			36		A
Q _{RR}	Reverse Recovery Charge			1		μC
E _{rec}	Reverse Recovery Energy			1.3		mJ
R _{thJC}	Junction to Case Thermal Resistance （ Per Diode ）				0.447	K /W
R _{thJH}	Junction to heatsink with SE8117 （ Per IGBT ）			0.648		K /W

NTC CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
R_{25}	Resistance	$T_C=25^{\circ}\text{C}$		5		k Ω
$B_{25/50}$	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 \text{ K}))]$			3375		K

MODULE CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		175	$^{\circ}\text{C}$
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
internal isolation		basic insulation	ZTA	
external metal coating of DBC		special protection	Ni	
Creepage distance		terminaltoheatsink	11.5	mm
		terminaltoterminale	5.5	mm
Clearance		terminaltoheatsink	10	mm
		terminaltoterminale	5	mm
RTI	RTI Elec.	housing	140	$^{\circ}\text{C}$
L_{sCE}	Stray inductance module		20	nH
CTI	Comparative Tracking Index		> 200	
F	Mounting Force Per Clamp		40~80	N
Weight			42.5	g
UL			E332185	

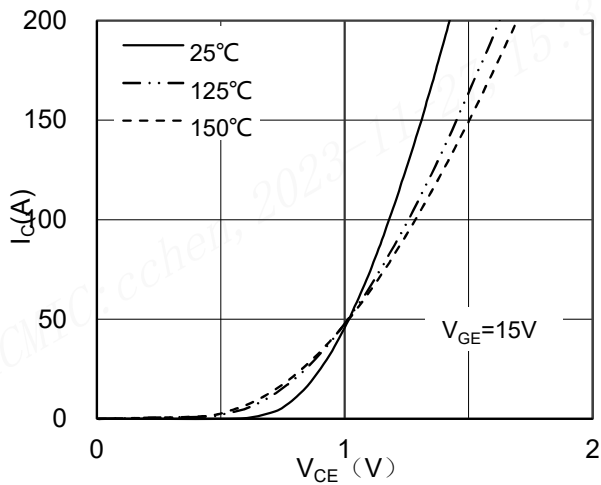


Figure 1. Typical Output Characteristics IGBT

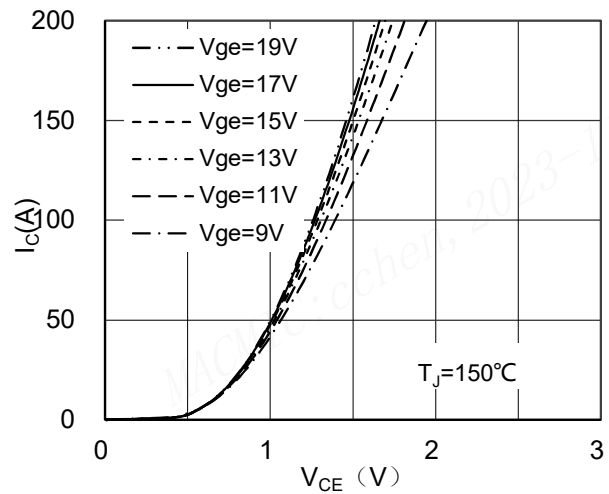


Figure 2. Typical Output Characteristics IGBT

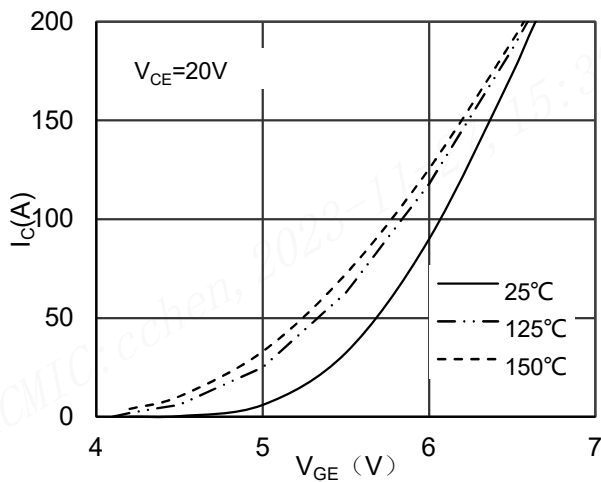


Figure 3. Typical Transfer characteristics IGBT

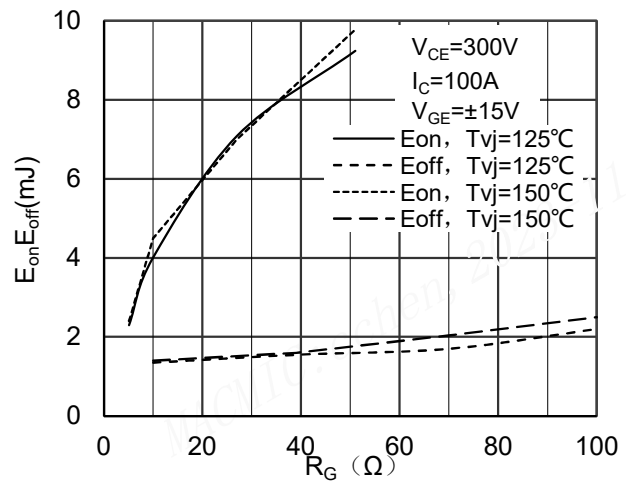


Figure 4. Switching Energy vs Gate Resistor IGBT (T1, T4)

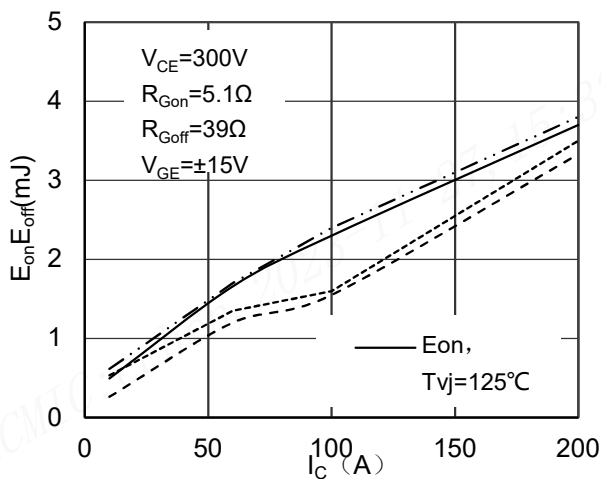


Figure 5. Switching Energy vs Collector Current IGBT (T1, T4)

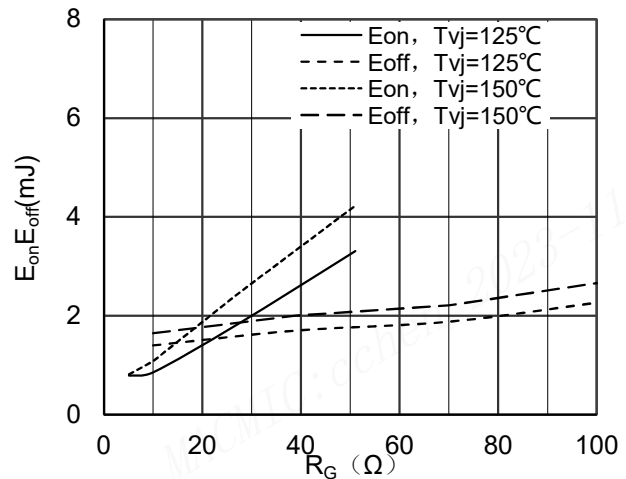


Figure 6. Switching Energy vs Gate Resistor IGBT (T2, T3)

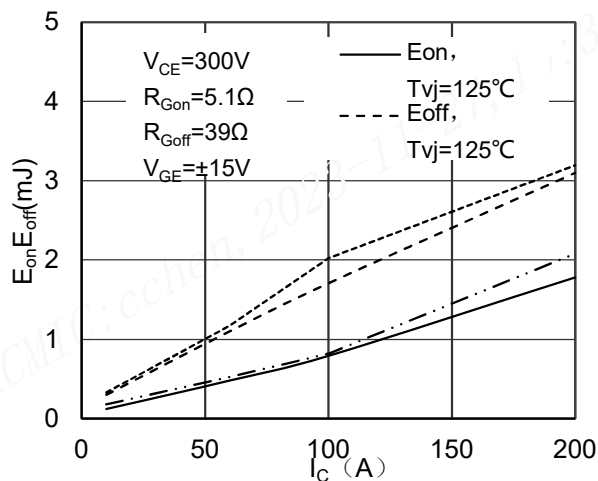


Figure 7. Switching Energy vs Collector Current IGBT
(T₂, T₃)

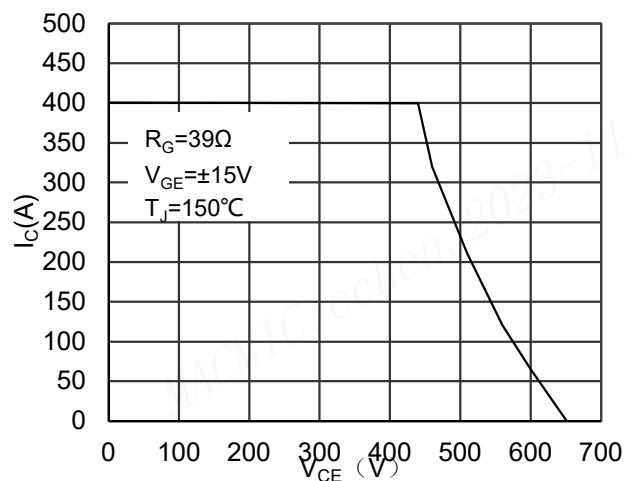


Figure 8. Reverse Biased Safe Operating Area IGBT-inverter

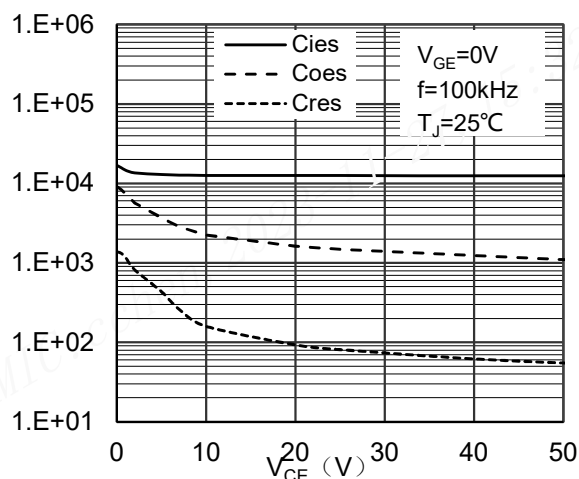


Figure 9. Typical capacitance

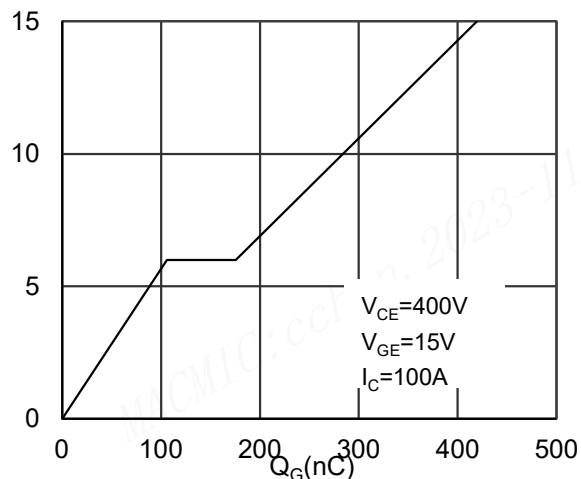


Figure 10. Typical Gate Charge

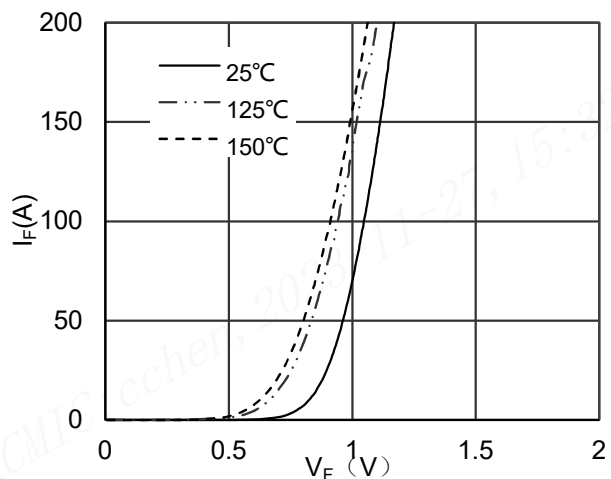


Figure 11. Diode Forward Characteristics Diode
(D₂, D₃, D₅, D₆)

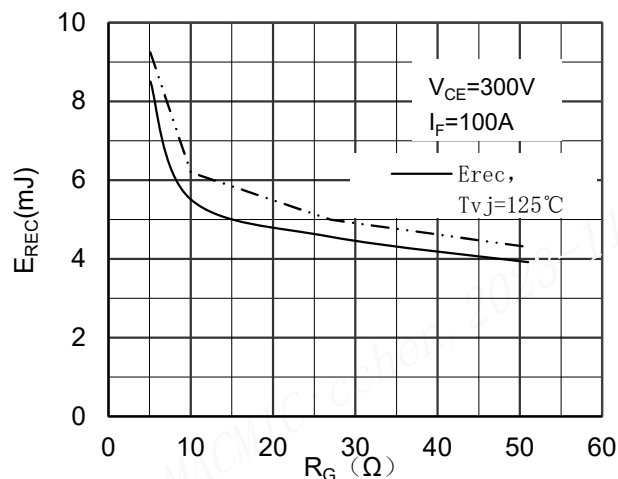


Figure 12. Switching Energy vs Gate Resistor Diode
(D₂, D₃, D₅, D₆)

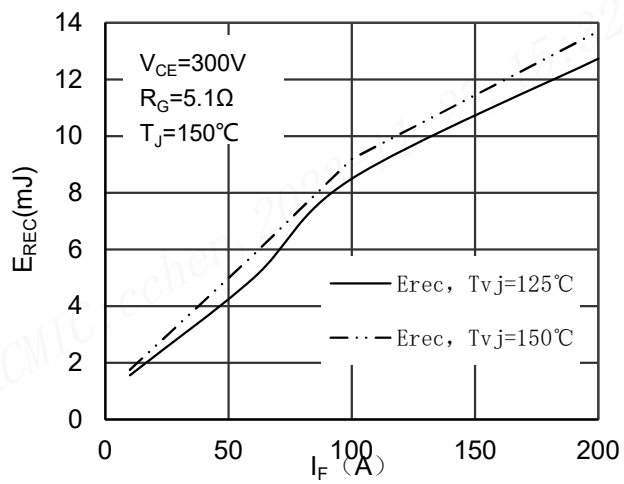


Figure 13. Switching Energy vs Forward Current Diode
(D2、D3、D5、D6)

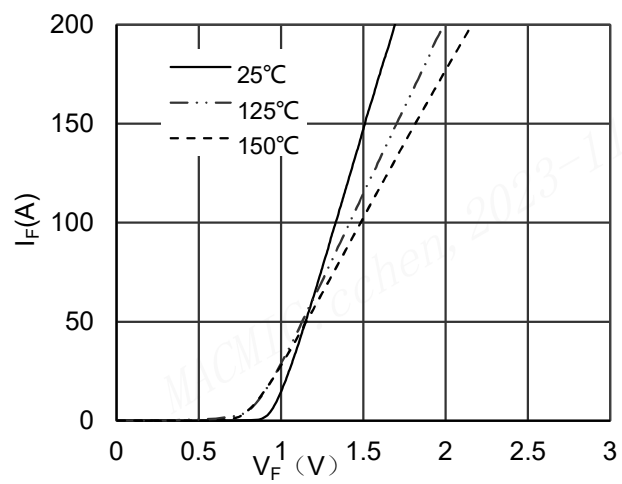


Figure 14. Diode Forward Characteristics Diode
(D1、D4)

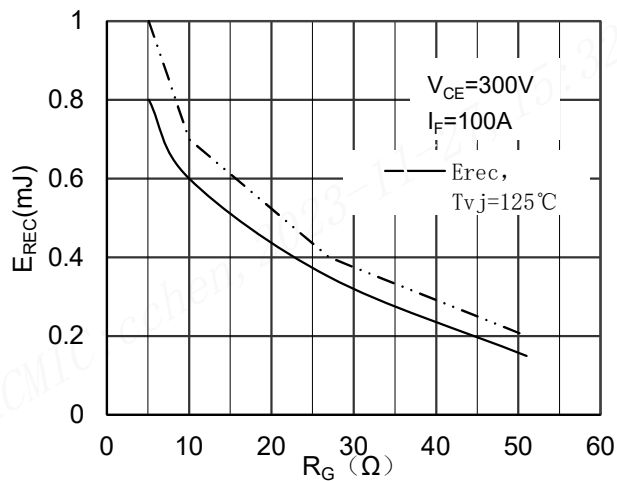


Figure 15. Switching Energy vs Gate Resistor Diode
(D1、D4)

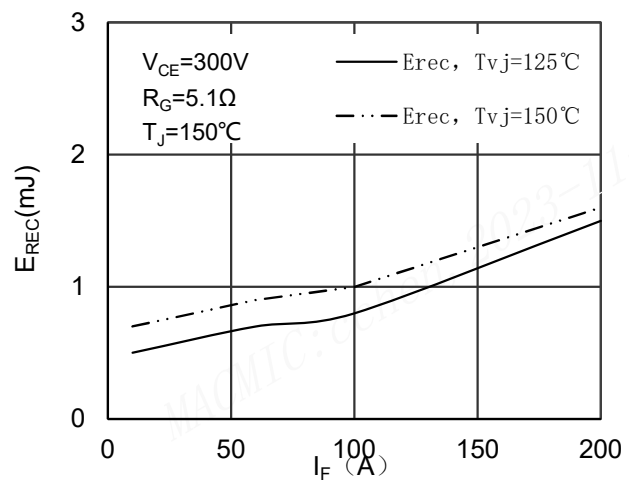


Figure 16. Switching Energy vs Forward Current Diode
(D1、D4)

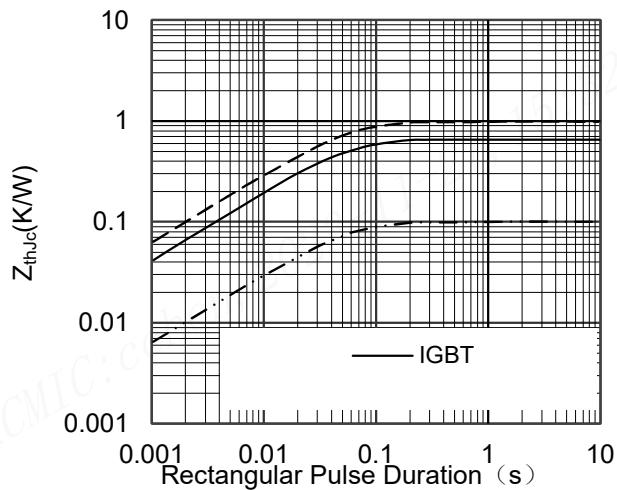


Figure 17. Transient Thermal Impedance of
Diode and IGBT

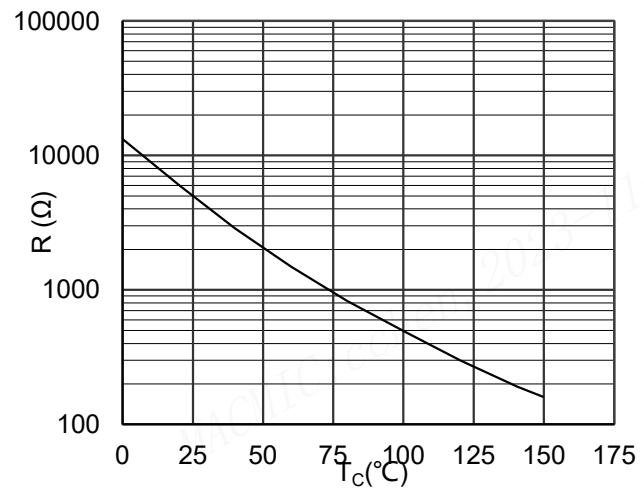
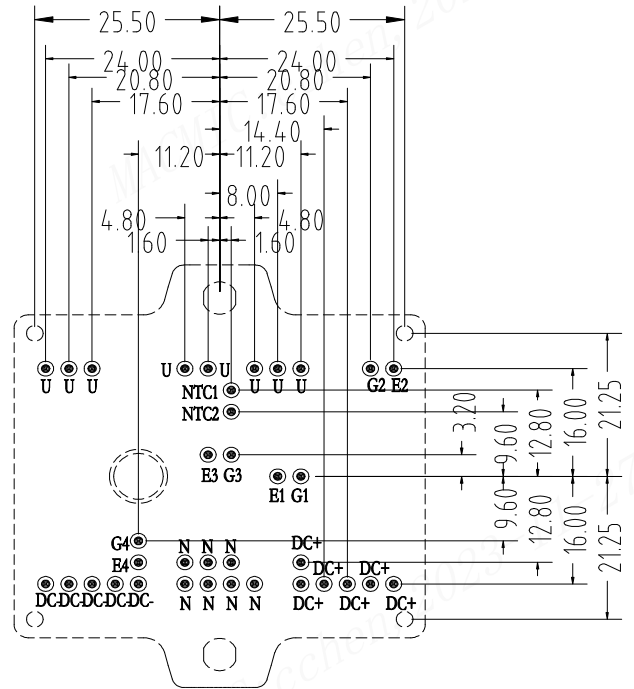
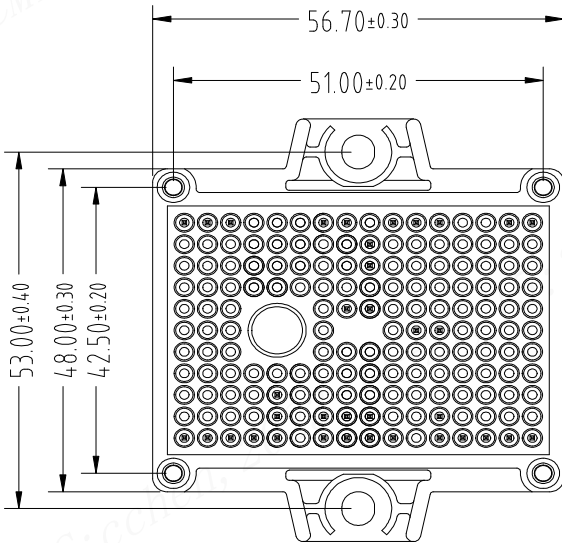
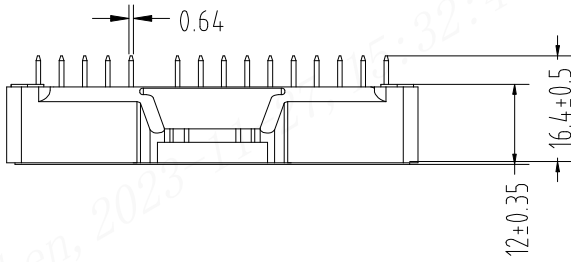
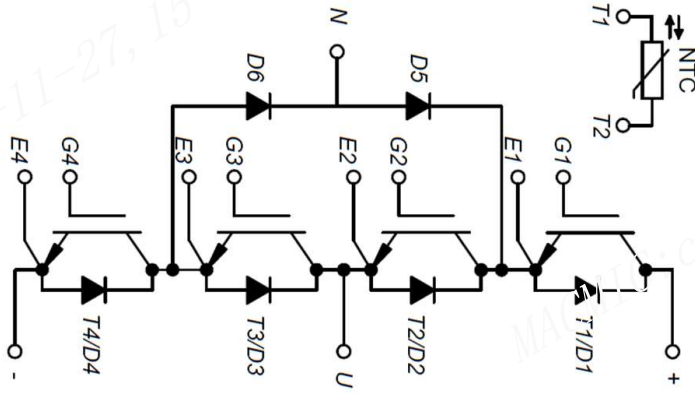


Figure 18. NTC Characteristics



Dimensions in (mm)

Figure 20. Package Outline

MMG200CE065PD6T5Z

Marking			
part1	logo		
part2	specifications of the products		
part3	Weekly batch number (with BOM version number)		
part4	DMcode (specifications_lot number_)		
	cont	digit	example
	specifications of the products	1-17	MMG200CE065PD6T5Z
	separator	18	—
	Production site	19	X—xinzhu; null—huashan
	product type	20	P—project; V—verify; null—mass
	Packaging type	21-23	GCE
	production year	24-25	23
	lot number	26-29	0001
part5	serial number	30-32	001
	lot number+serial number		
part6	UL mark		

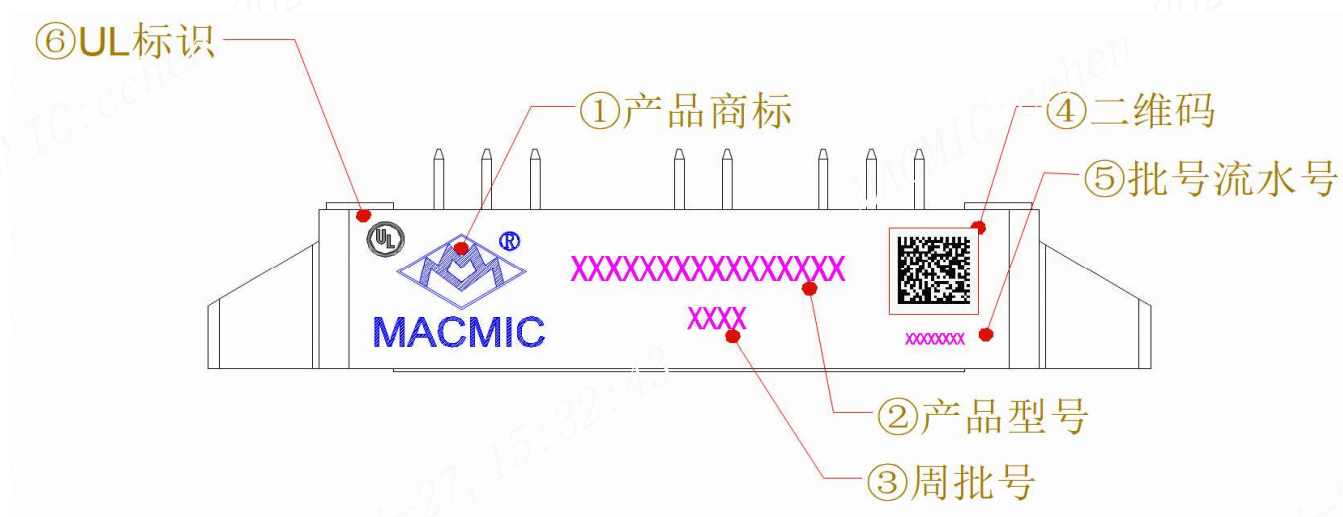


Figure 21. Marking instructions